

TECHNICAL REPORT

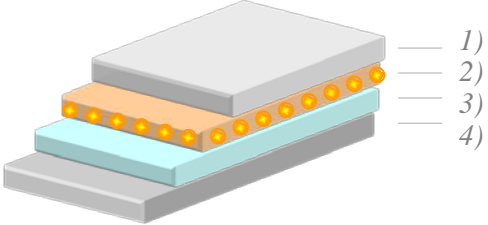


CP6920F3

Anisotropic Conductive Film for Chip on Glass

*Products Development Department
Advanced Material Division*

Specifications

Items		CP6920F3	Remarks
Curing system		Epoxy-Anion	
Structure and thickness	1) Cover film / color	25μm / transparent	
	2) ACF-layer	10μm	
	3) NCF-layer	10μm	
	4) Base film / color	38μm / white	
Conductive particles	1) Material	Au/Ni plated resin	
	2) Insulator coated	Yes	
	Particle diameter	3μm	
Minimum overlap area of conductors		1300μm ²	*1
Minimum conductor space		12μm	Space between neighboring circuits.
Minimum bump space		10μm	Space between bumps.

*1: The contact area needs to trap at least three particles (average -4.5δ) and where the faced conductor overlaps.

Bonding conditions and Properties

Bonding conditions *1

items		CP6920F3	Remarks
ACF laminating conditions	Temperature	60~80°C	*2
	Pressure	0.3~1.0MPa	*3
	Time	1~2sec	*4
Main bonding conditions	Temperature	190°C~	*2
	Pressure	60~80MPa	*5
	Time	5sec	*4

*1: Bonding condition may differ depending on chip size and metal pattern. We recommend this as a starting point to determine your own optimized conditions.

*2: Temperature of ACF lamination and main bonding: It is not equipment temperature, but actual temperature of ACF.

*3: Pressure of ACF lamination: It is calculated based on the area of ACF lamination.

*4: Time of ACF lamination and main bonding: Time from the start of bonding to the point where the temperature reaches the target.

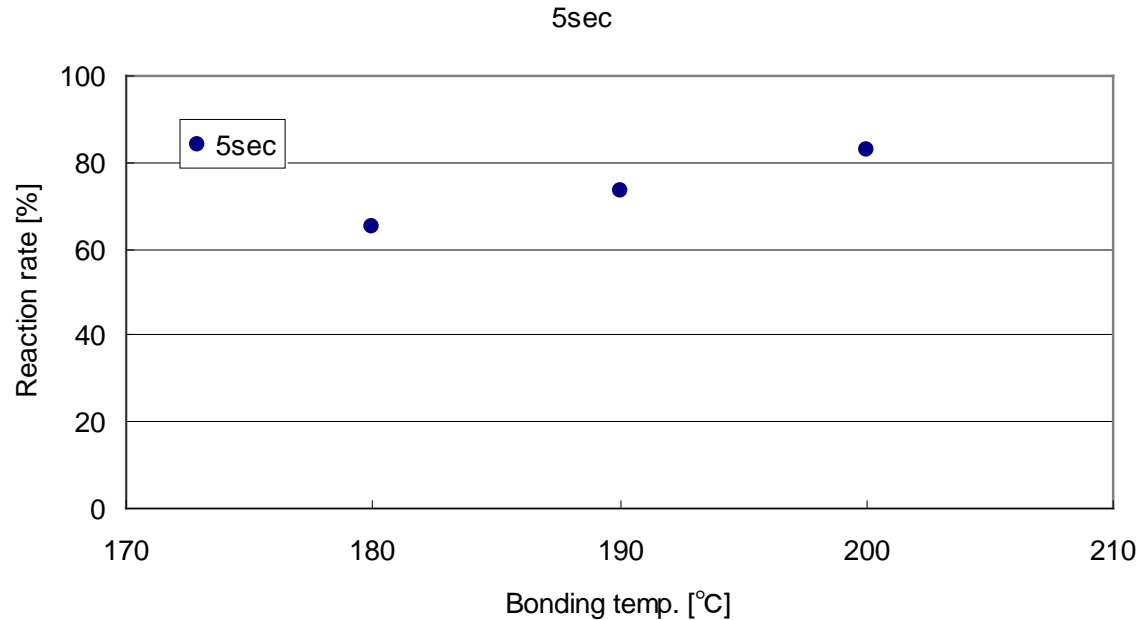
*5: The pressure is calculated based on the total area of bumps.

Properties of cured ACF

items		CP6920F3	Remarks
Elastic modulus	at 30°C	2.6GPa	DMA
Glass transition temperature (Tg)		146°C	DMA, tanδ peak

Reaction rate

IC : 1.8mm × 20mm, t= 0.5mm
 Pattern ITO : ITO=10Ω/□, t= 0.7mm glass
 Bonding Condition : 180°C-200°C,80MPa,5sec
 Measurement : FT-IR Method

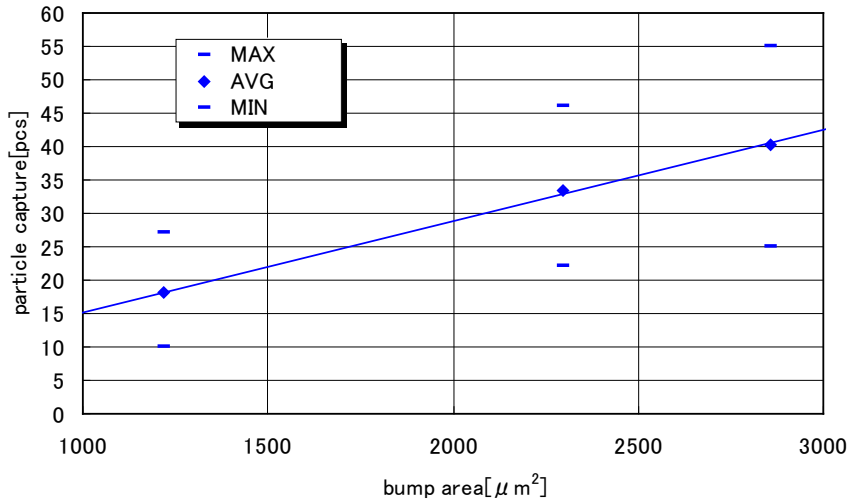


Note: This report has been prepared on the basis of our reliable tests, however is not intended to guarantee the performance described hereunder.

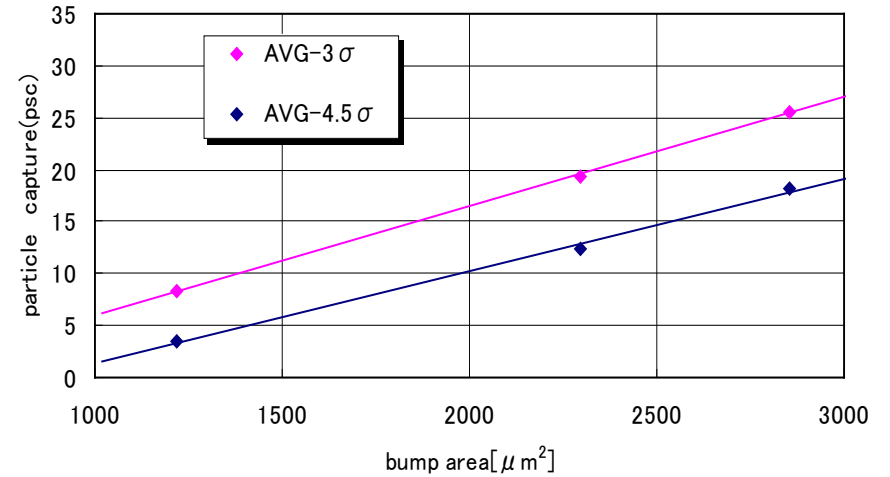
Particle capture

IC : 1.8mm × 20mm, t= 0.5mm, Au-plated bump
 Pattern ITO : ITO=10Ω/□, t=0.7mm glass

Particle Capture on bump



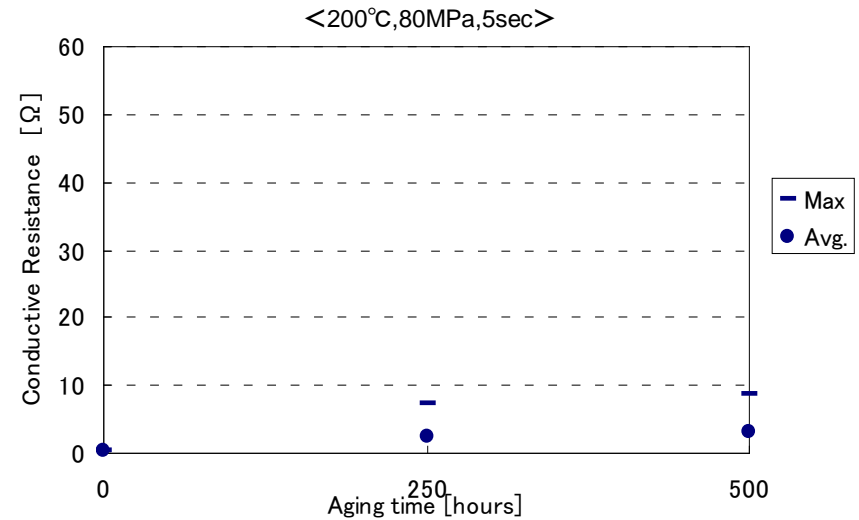
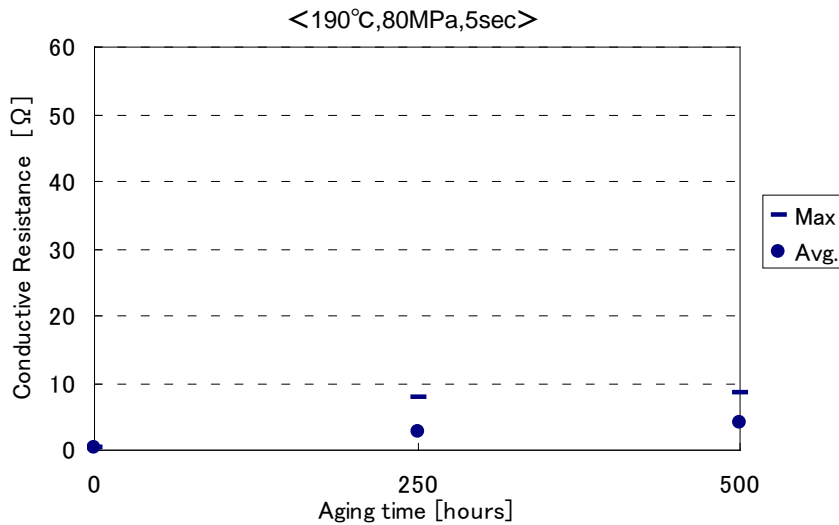
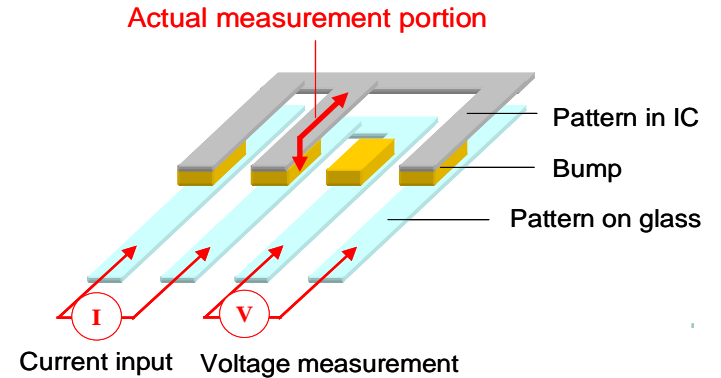
Particle Capture on a bump(Statistics)



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Conductive resistance

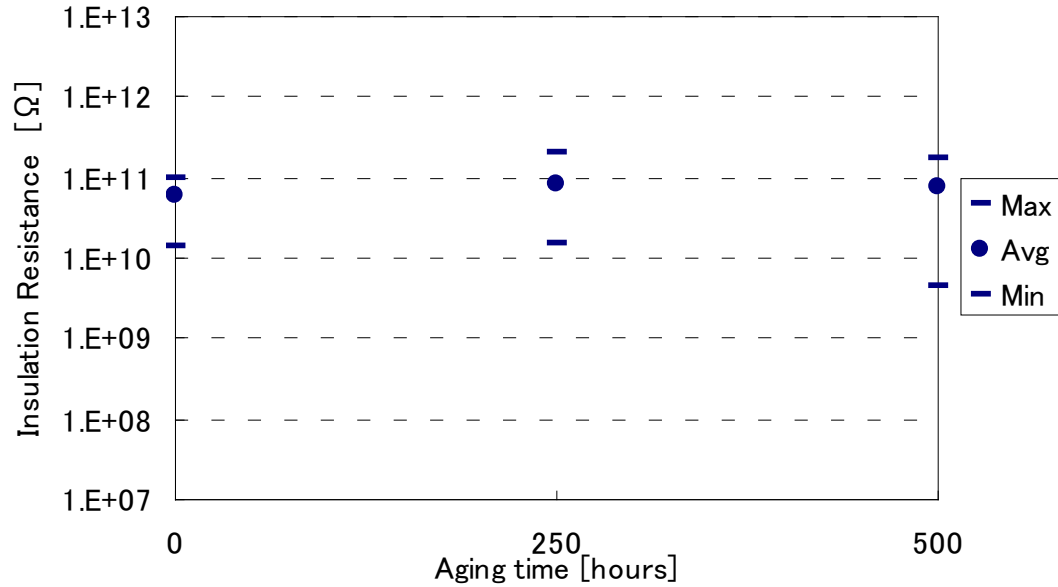
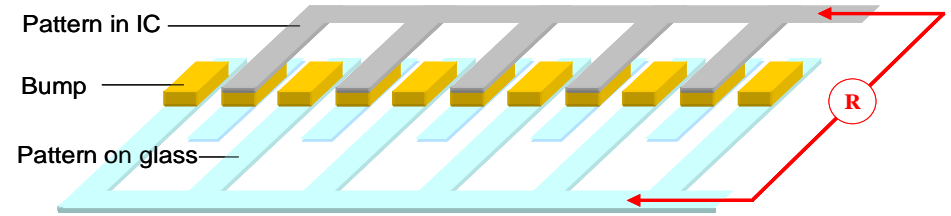
IC : 1.8mm × 20mm, t= 0.5mm
 Bump 30μm × 85μm, Au-plated bump
 Pattern ITO : ITO=10Ω/□, t=0.7mm glass
 Bonding Condition : 190°C,200°C-80MPa-5sec
 Aging Condition : 85°C85%RH



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Insulation resistance

IC : 1.5mm × 13mm, t= 0.5mm, Au-plated bump
 Pattern ITO : ITO=10Ω/□, t=0.7mm glass
 Bonding Condition : 190°C-80MPa-5sec
 Aging Condition : 85°C85%RH



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